

### SOT-23 Plastic-Encapsulate Transistors

#### BCW61B TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$$P_{CM}: 0.25 \text{ W (Tamb=25°C)}$$

Collector current

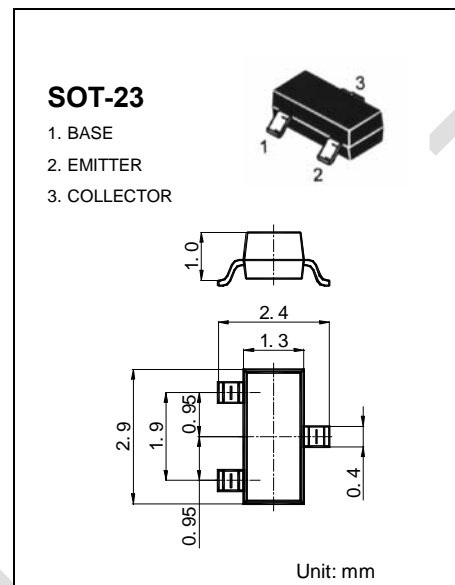
$$I_{CM}: -0.2 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -32 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-32			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -32\text{V}, I_E = 0$			-0.02	$\mu\text{A}$
Collector cut-off current	$I_{EBO}$	$V_{EB} = -4\text{V}, I_C = 0$			-0.02	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	180		310	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50\text{mA}, I_B = -1.25\text{mA}$			-0.55	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50\text{mA}, I_B = -1.25\text{mA}$			-1.05	V
Transition frequency	$f_T$	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$ $f = 100\text{MHz}$	100			MHz

Marking	BB
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